



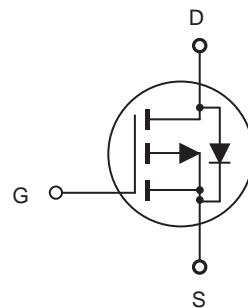
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CED3423/CEU3423

P-Channel Enhancement Mode Field Effect Transistor

FEATURES

- -30V, -18A, $R_{DS(ON)} = 45m\Omega$ @ $V_{GS} = -10V$.
 $R_{DS(ON)} = 80m\Omega$ @ $V_{GS} = -4.5V$.
- Super high dense cell design for extremely low $R_{DS(ON)}$.
- High power and current handing capability.
- Lead free product is acquired.
- TO-251 & TO-252 package.



ABSOLUTE MAXIMUM RATINGS $T_C = 25^\circ C$ unless otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-18	A
Drain Current-Pulsed ^a	I_{DM}	-72	A
Maximum Power Dissipation @ $T_C = 25^\circ C$ - Derate above $25^\circ C$	P_D	31 0.25	W W/ $^\circ C$
Operating and Store Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Limit	Units
Thermal Resistance, Junction-to-Case	R_{JC}	4	$^\circ C/W$
Thermal Resistance, Junction-to-Ambient	R_{JA}	50	$^\circ C/W$

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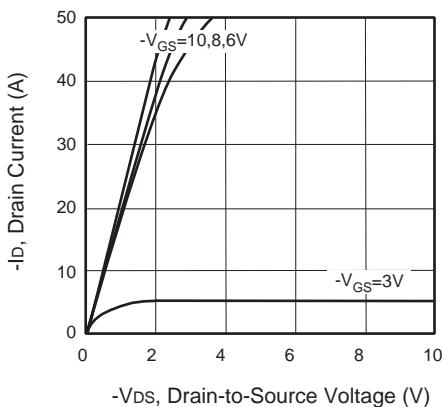


Figure 1. Output Characteristics

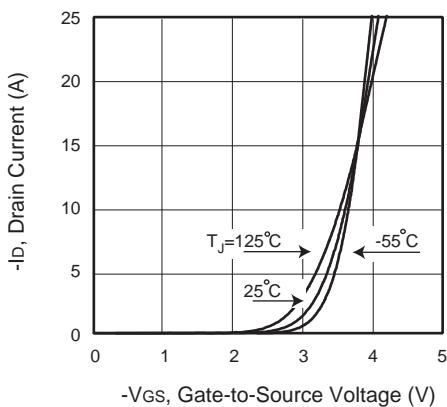


Figure 2. Transfer Characteristics

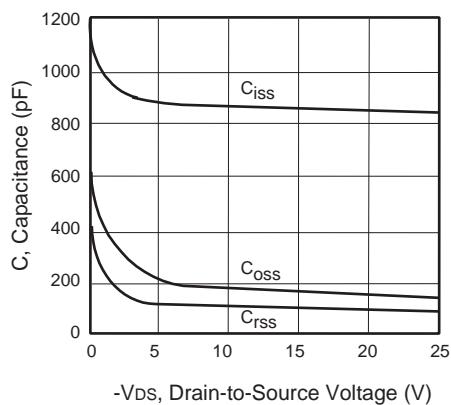


Figure 3. Capacitance

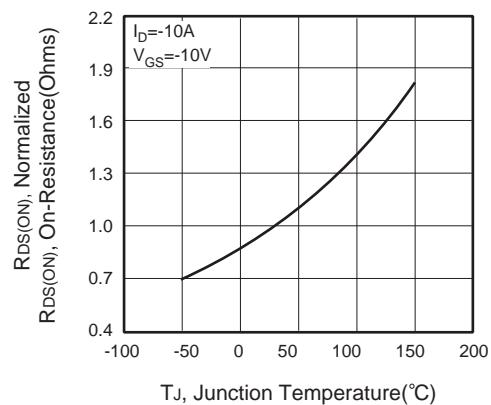


Figure 4. On-Resistance Variation with Temperature

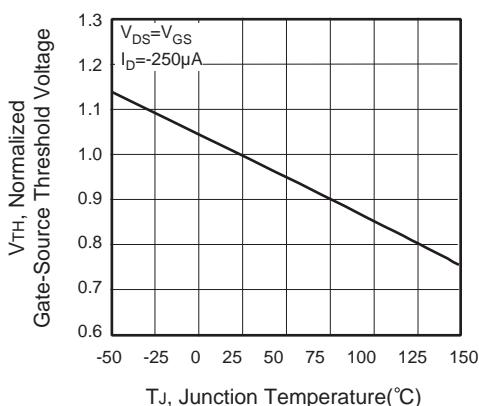


Figure 5. Gate Threshold Variation with Temperature

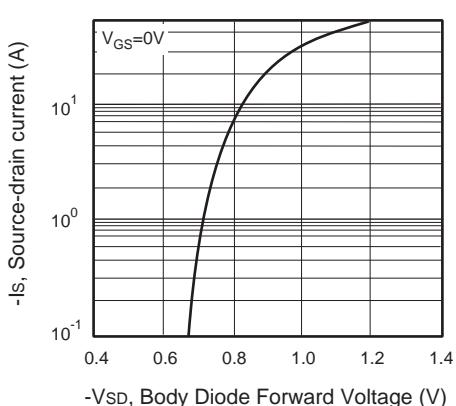


Figure 6. Body Diode Forward Voltage Variation with Source Current



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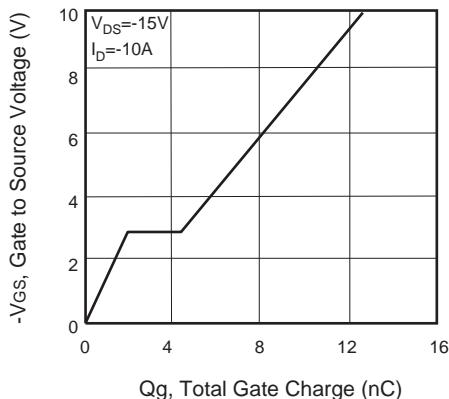


Figure 7. Gate Charge

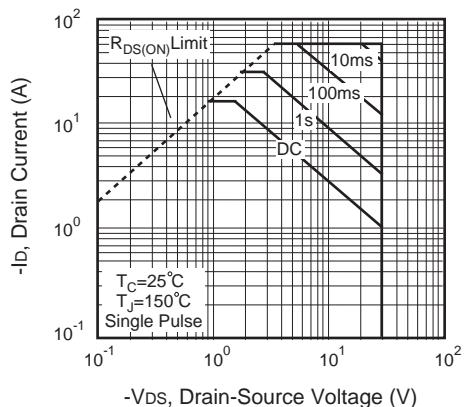


Figure 8. Maximum Safe Operating Area

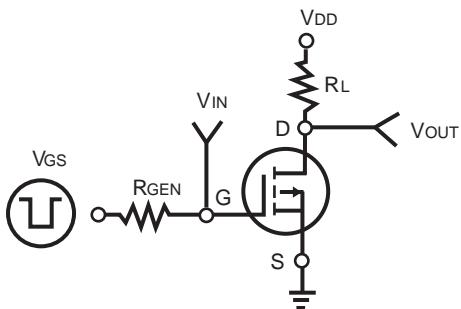


Figure 9. Switching Test Circuit

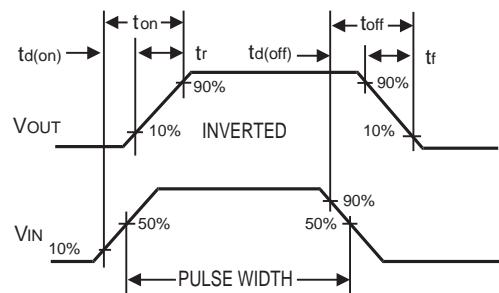


Figure 10. Switching Waveforms

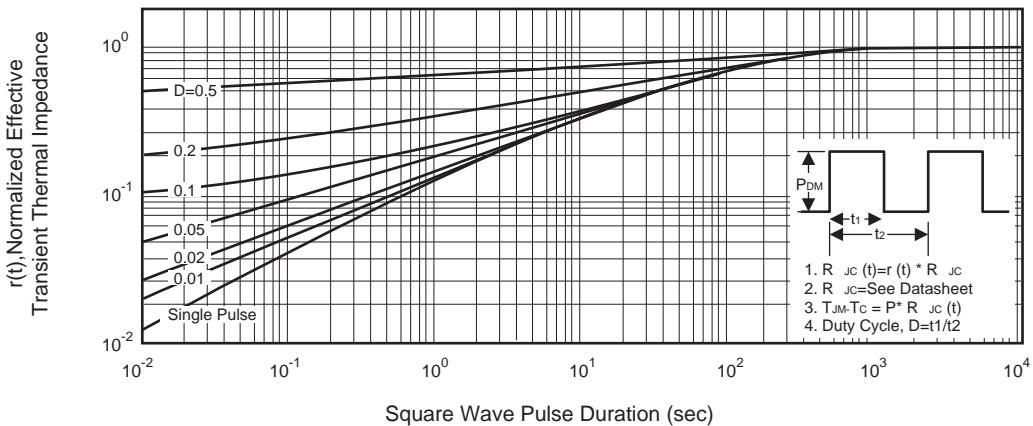


Figure 11. Normalized Thermal Transient Impedance Curve